Icemos Technology Ltd **Product Specification** **1000.666802** Issue Date 17 February 2023 12:

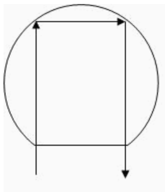
Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Secondary Flat Length	none / 18.5 +/- 2.5mm	Wafer Vendor
	6.0	Overall Thickness	319.50 +/- 6.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
	12.0	Backside Laser Marking Type	On wafer BACKSIDE. Scribe format: [SUNSHINEXXXX] (unique scribe)	Guaranteed by process
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	15.0	Handle Thickness	300.00 +/- 5.00 µm	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0	Handle Dopant	Antimony	Wafer Vendor
	18.0	Handle Resistivity	0.01 - 0.025 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with lasermarking and oxide.	Wafer Vendor
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0	Nominal Thickness	17.50 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2.0 mm	Typical by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Antimony	Wafer Vendor
	29.0	Device Resistivity	0.01 - 0.025 Ohmcm	Wafer Vendor
	30.0	Voids	0	Bright Light, 100% (note 2)
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

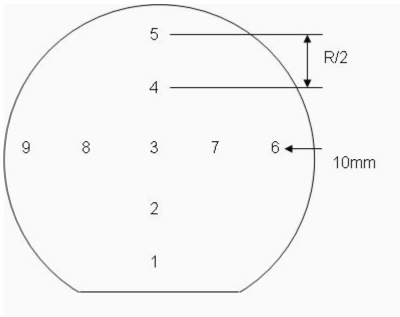
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information